



PJD100N04-AU

40V N-Channel Enhancement Mode MOSFET

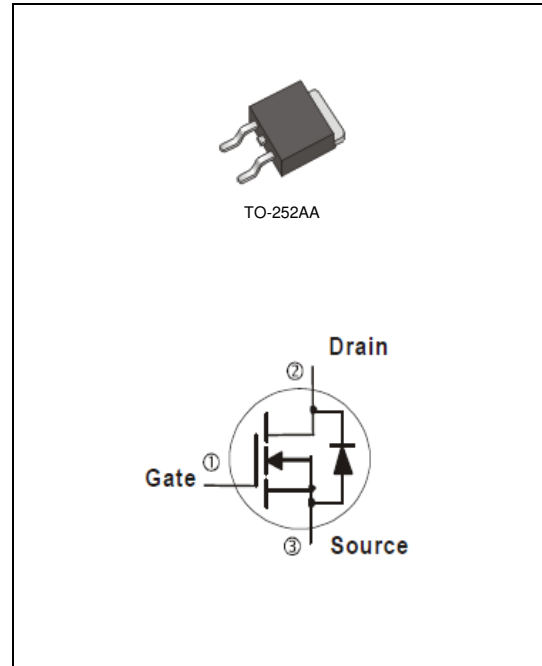
Voltage 40 V **Current** 100 A

Features

- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@20A < 3.8m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@10A < 5m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 Standard

Mechanical Data

- Case : TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Weight : 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current (Note 4)	I_D	$T_C=25^\circ C$	100
		$T_C=100^\circ C$	64
Pulsed Drain Current (Note 1)	I_{DM}	400	A
Power Dissipation	P_D	$T_C=25^\circ C$	83.3
		$T_C=100^\circ C$	41.7
Continuous Drain Current (Note 4)	I_D	$T_A=25^\circ C$	17
		$T_A=70^\circ C$	13
Power Dissipation	P_D	$T_A=25^\circ C$	2.4
		$T_A=70^\circ C$	1.6
Single Pulse Avalanche Energy (Note 6)	E_{AS}	312	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~175	$^\circ C$
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{\theta JC}$	1.8
	Junction to Ambient	$R_{\theta JA}$	62.5

- Limited only By Maximum Junction Temperature



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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.54	2.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	2.1	3.8	m Ω
		$V_{GS}=4.5V, I_D=10A$	-	2.8	5	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$	-	-	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Dynamic (Note 7)						
Total Gate Charge	Q_g	$V_{DS}=20V, I_D=10A,$ $V_{GS}=4.5V$ (Note 2,3)	-	50	-	nC
Gate-Source Charge	Q_{gs}		-	13	-	
Gate-Drain Charge	Q_{gd}		-	19	-	
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $f=1\text{MHZ}$	-	5214	-	pF
Output Capacitance	C_{oss}		-	492	-	
Reverse Transfer Capacitance	C_{rss}		-	246	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=20V, I_D=1A,$ $V_{GS}=10V, R_G=6\Omega$ (Note 2,3)	-	44	-	ns
Turn-On Rise Time	t_r		-	43	-	
Turn-Off Delay Time	$t_{d(off)}$		-	218	-	
Turn-Off Fall Time	t_f		-	62	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	100	A
Diode Forward Voltage	V_{SD}	$I_S=1A, V_{GS}=0V$	-	0.65	1	V

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.
4. The maximum current rating is package limited.
5. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz. square pad of copper.
6. The test condition is $L=0.1\text{mH}, I_{AS}=79A, V_{DD}=25V, V_{GS}=10V$, Starting $T_J=25^\circ\text{C}$.
7. Guaranteed by design, not subject to production testing.



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TYPICAL CHARACTERISTIC CURVES

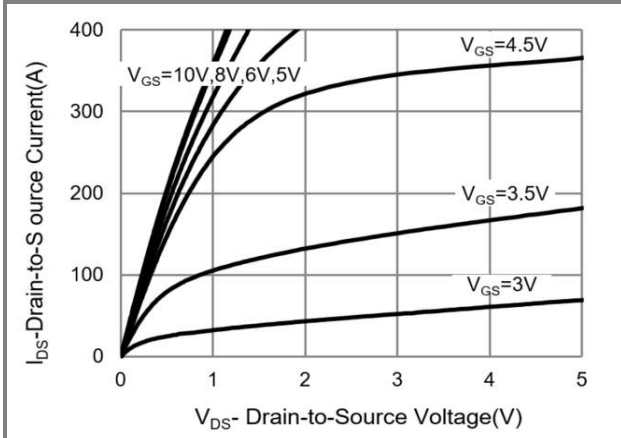


Fig.1 Output Characteristics

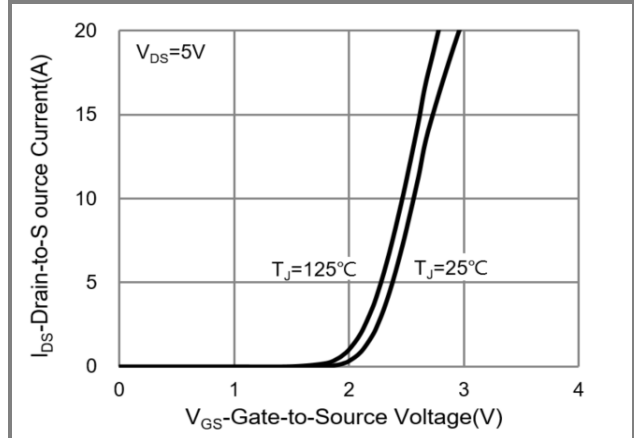


Fig.2 Transfer Characteristics

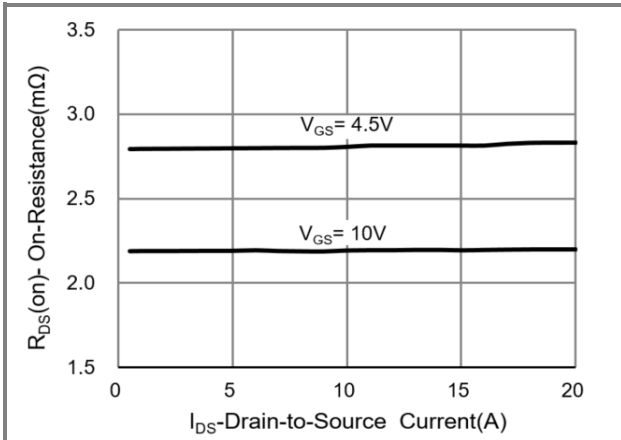


Fig.3 On-Resistance vs. Drain Current

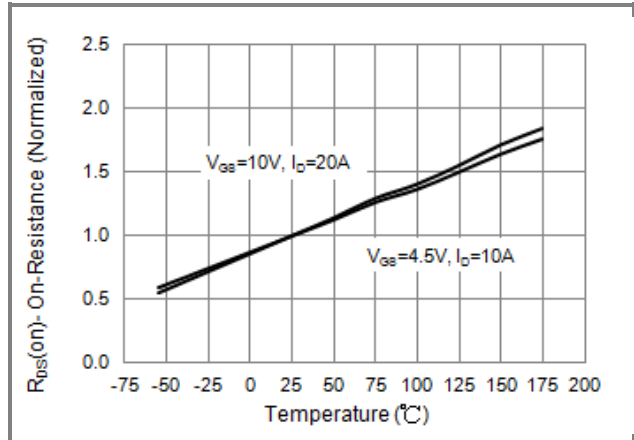


Fig.4 On-Resistance vs. Junction temperature

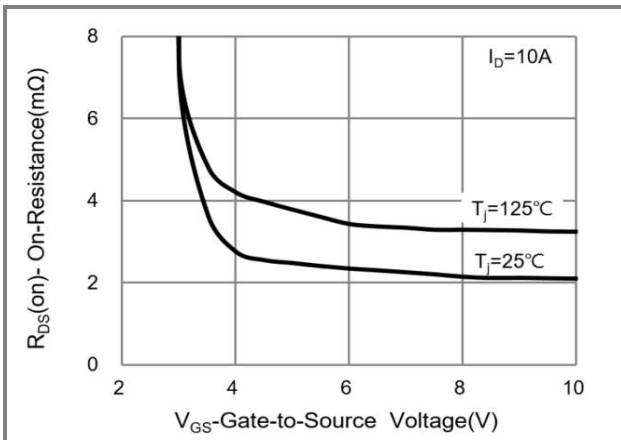


Fig.5 On-Resistance Variation with V_{GS}

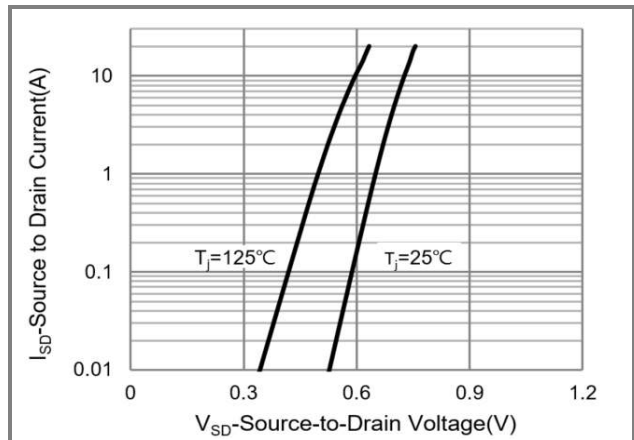


Fig.6 Source-Drain Diode Forward Voltage



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TYPICAL CHARACTERISTIC CURVES

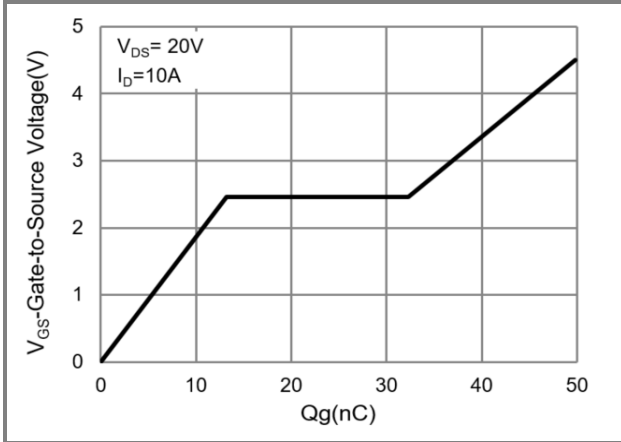


Fig.7 Gate-Charge Characteristics

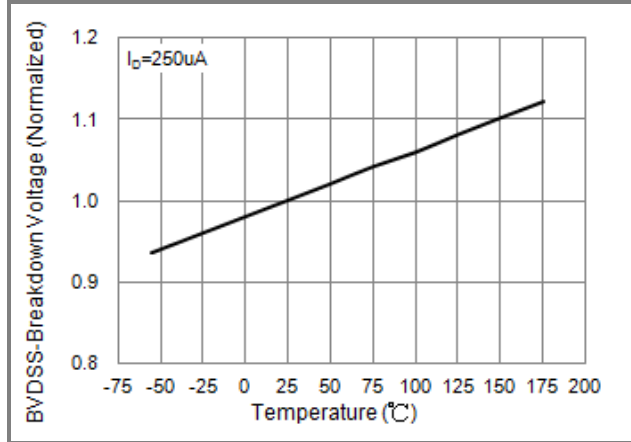


Fig.8 Breakdown Voltage Variation vs. Temperature

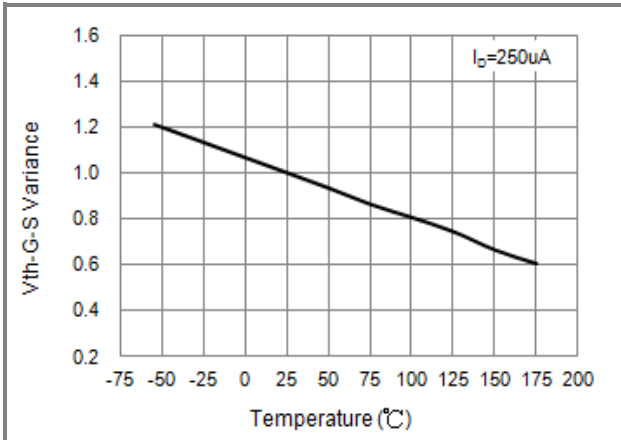


Fig.9 Threshold Voltage Variation with Temperature

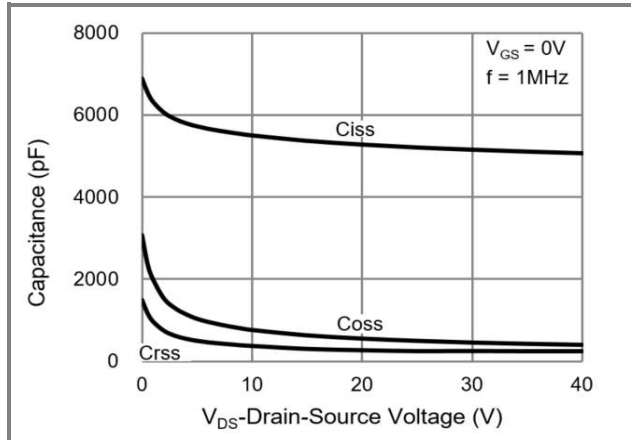


Fig.10 Capacitance vs. Drain-Source Voltage

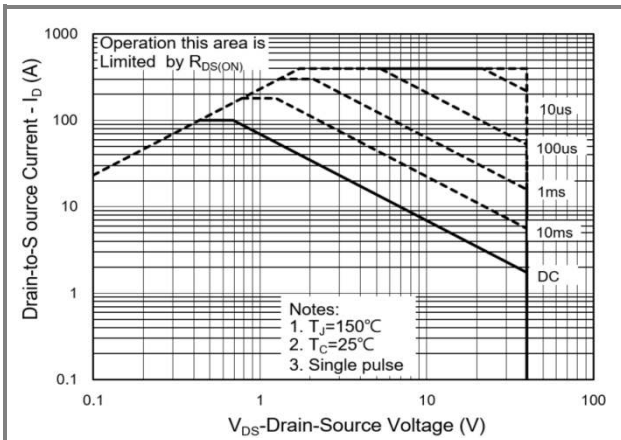


Fig.11 Maximum Safe Operating Area

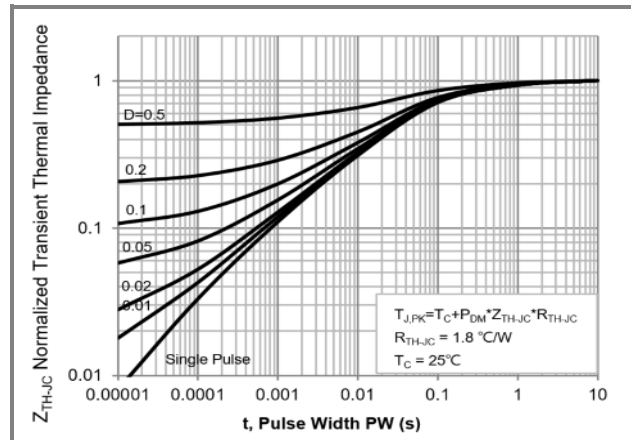


Fig.12 Normalized Transient Thermal Impedance

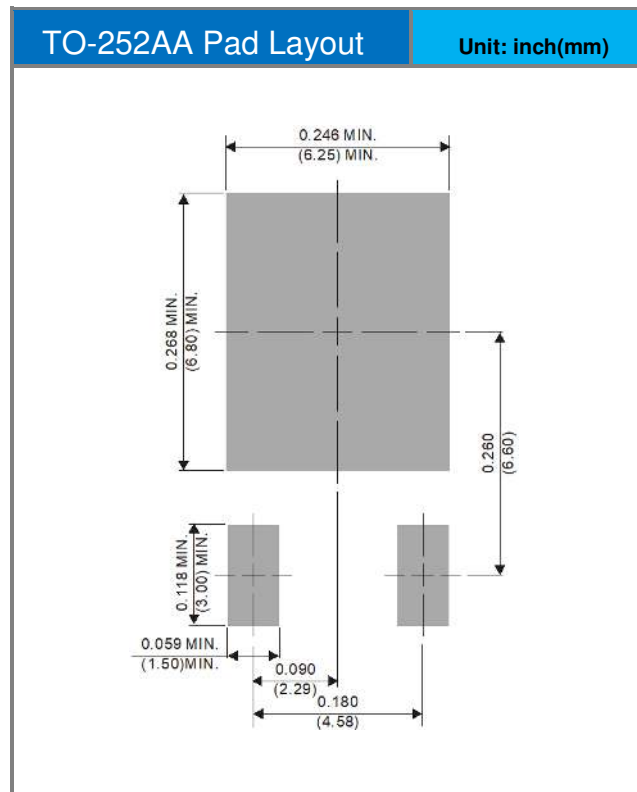
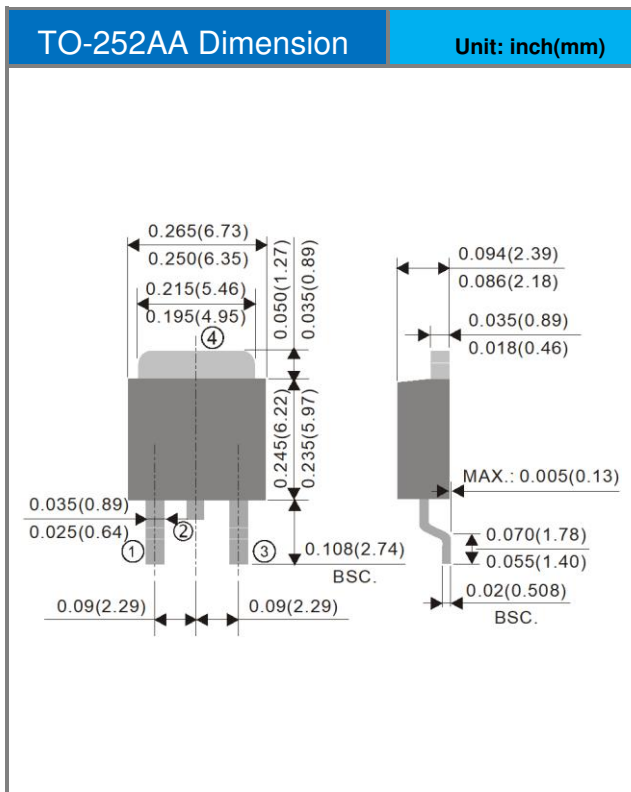


PJD100N04-AU

Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD100N04-AU_L2_000A1	TO-252AA	3,000pcs / 13" reel	D100N04	Halogen free

Packaging Information & Mounting Pad Layout





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